74LVC2G08

Dual 2-input AND gate

Rev. 05 — 15 May 2006 Product data sheet

1. General description

The 74LVC2G08 is a high-performance, low-power, low-voltage, Si-gate CMOS device and superior to most advanced CMOS compatible TTL families.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of these devices as translators in a mixed 3.3 V and 5 V environment.

This device is fully specified for partial power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

The 74LVC2G08 provides the 2-input AND gate function.

2. Features

- Wide supply voltage range from 1.65 V to 5.5 V
- 5 V tolerant outputs for interfacing with 5 V logic
- High noise immunity
- ±24 mA output drive (V_{CC} = 3.0 V)
- CMOS low power consumption
- Complies with JEDEC standard:
  - JESD8-7 (1.65 V to 1.95 V)
  - JESD8-5 (2.3 V to 2.7 V)
  - JESD8-B/JESD36 (2.7 V to 3.6 V)
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- ESD protection:
  - HBM EIA/JESD22-A114-C exceeds 2000 V
  - MM EIA/JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from –40 °C to +85 °C and –40 °C to +125 °C

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3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74LVC2G08DP	–40 °C to +125 °C	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74LVC2G08DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74LVC2G08GT	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 × 1.95 × 0.5 mm	SOT833-1
74LVC2G08GM	–40 °C to +125 °C	XQFN8	plastic extremely thin quad flat package; no leads; 8 terminals; body 1.6 × 1.6 × 0.5 mm	SOT902-1

4. Marking

Table 2. Marking

Type number	Marking code
74LVC2G08DP	V08
74LVC2G08DC	V08
74LVC2G08GT	V08
74LVC2G08GM	V08

5. Functional diagram

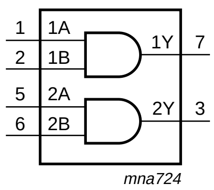

Fig 1. Logic symbol

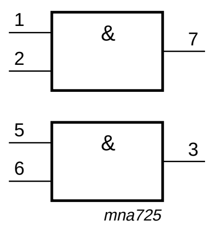

Fig 2. IEC logic symbol

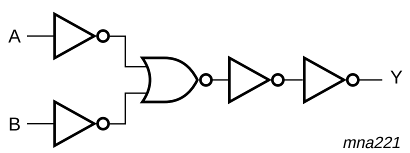

Fig 3. Logic diagram (one gate)

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6. Pinning information

6.1 Pinning

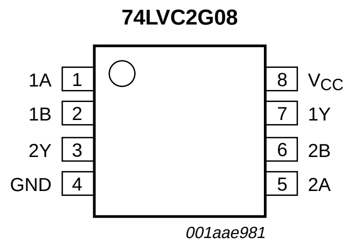

Fig 4. Pin configuration TSSOP8 and VSSOP8

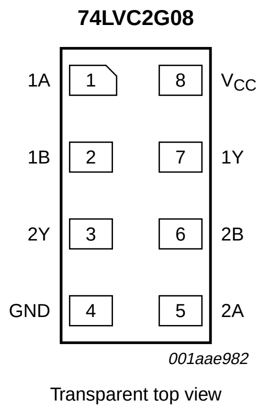

Fig 5. Pin configuration XSON8

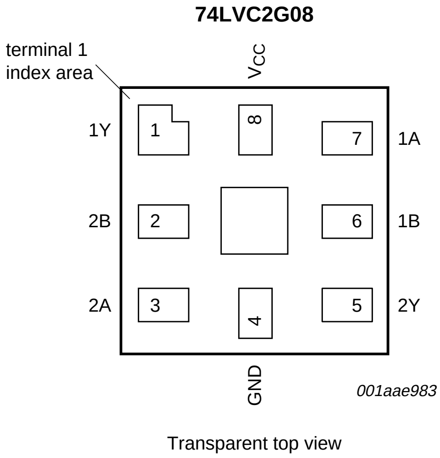

Fig 6. Pin configuration XQFN8

6.2 Pin description

Table 3. Pin description

Symbol	Pin			Description
	TSSOP8, VSSOP8	XSON8	XQFN8	
1A	1	1	7	data input 1A
1B	2	2	6	data input 1B
2Y	3	3	5	data output 2Y
GND	4	4	4	ground (0 V)
2A	5	5	3	data input 2A

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Table 3. Pin description *...continued*

Symbol	Pin			Description
	TSSOP8, VSSOP8	XSON8	XQFN8	
2B	6	6	2	data input 2B
1Y	7	7	1	data output 1Y
V_{CC}	8	8	8	supply voltage

7. Functional description

7.1 Function table

Table 4. Function table[1]

Input		Output
nA	nB	nY
L	L	L
L	H	L
H	L	L
H	H	H

[1] H = HIGH voltage level;
L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			–0.5	+6.5	V
V_I	input voltage		[1]	–0.5	+6.5	V
V_O	output voltage	Active mode	[1]	–0.5	V_{CC} + 0.5	V
		Power-down mode	[1][2]	–0.5	+6.5	V
I_{IK}	input clamping current	$V_I < 0$ V		-	–50	mA
I_{OK}	output clamping current	$V_O < 0$ V or $V_O > V_{CC}$		-	±50	mA
I_O	output current	$V_O = 0$ V to V_{CC}		-	±50	mA
I_{CC}	quiescent supply current			-	100	mA
I_{GND}	ground current			-	–100	mA
T_{stg}	storage temperature			–65	+150	°C
P_{tot}	total power dissipation	T_{amb} = –40 °C to +125 °C	[3]	-	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When V_{CC} = 0 V (Power-down mode), the output voltage can be 5.5 V in normal condition.

[3] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.
For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K.
For XSON8 and XQFN8 packages: above 45 °C the value of P_{tot} derates linearly with 2.4 mW/K.

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9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		1.65	-	5.5	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage	Active mode	0	-	V_{CC}	V
		Power-down mode	0	-	5.5	V
T_{amb}	ambient temperature		–40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 1.65 V to 2.7 V	0	-	20	ns/V
		V_{CC} = 2.7 V to 5.5 V	0	-	10	ns/V

10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = –40 °C to +85 °C[1]						
V_{IH}	HIGH-state input voltage	V_{CC} = 1.65 V to 1.95 V	0.65 × V_{CC}	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.7	-	-	V
		V_{CC} = 2.7 V to 3.6 V	2.0	-	-	V
		V_{CC} = 4.5 V to 5.5 V	0.7 × V_{CC}	-	-	V
V_{IL}	LOW-state input voltage	V_{CC} = 1.65 V to 1.95 V	-	-	0.35 × V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V_{CC} = 2.7 V to 3.6 V	-	-	0.8	V
		V_{CC} = 4.5 V to 5.5 V	-	-	0.3 × V_{CC}	V
V_{OH}	HIGH-state output voltage	V_I = V_{IH} or V_{IL}				
		I_O = –100 μA; V_{CC} = 1.65 V to 5.5 V	V_{CC} – 0.1	-	-	V
		I_O = –4 mA; V_{CC} = 1.65 V	1.2	1.53	-	V
		I_O = –8 mA; V_{CC} = 2.3 V	1.9	2.13	-	V
		I_O = –12 mA; V_{CC} = 2.7 V	2.2	2.50	-	V
		I_O = –24 mA; V_{CC} = 3.0 V	2.3	2.60	-	V
		I_O = –32 mA; V_{CC} = 4.5 V	3.8	4.10	-	V
V_{OL}	LOW-state output voltage	V_I = V_{IH} or V_{IL}				
		I_O = 100 μA; V_{CC} = 1.65 V to 5.5 V	-	-	0.1	V
		I_O = 4 mA; V_{CC} = 1.65 V	-	0.08	0.45	V
		I_O = 8 mA; V_{CC} = 2.3 V	-	0.14	0.3	V
		I_O = 12 mA; V_{CC} = 2.7 V	-	0.19	0.4	V
		I_O = 24 mA; V_{CC} = 3.0 V	-	0.37	0.55	V
		I_O = 32 mA; V_{CC} = 4.5 V	-	0.43	0.55	V
I_{LI}	input leakage current	V_I = 5.5 V or GND; V_{CC} = 5.5 V	-	±0.1	±5	μA
I_{OFF}	power-off leakage current	V_I or V_O = 5.5 V; V_{CC} = 0 V	-	±0.1	±10	μA
I_{CC}	quiescent supply current	V_I = V_{CC} or GND; I_O = 0 A; V_{CC} = 5.5 V	-	0.1	10	μA

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Table 7. Static characteristics *...continued*

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
ΔI_{CC}	additional quiescent supply current	per pin; $V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 2.3$ V to 5.5 V	-	5	500	µA
C_i	input capacitance		-	2.5	-	pF
$T_{amb} = -40$ °C to +125 °C						
V_{IH}	HIGH-state input voltage	$V_{CC} = 1.65$ V to 1.95 V	$0.65 \times V_{CC}$	-	-	V
		$V_{CC} = 2.3$ V to 2.7 V	1.7	-	-	V
		$V_{CC} = 2.7$ V to 3.6 V	2.0	-	-	V
		$V_{CC} = 4.5$ V to 5.5 V	$0.7 \times V_{CC}$	-	-	V
V_{IL}	LOW-state input voltage	$V_{CC} = 1.65$ V to 1.95 V	-	-	$0.35 \times V_{CC}$	V
		$V_{CC} = 2.3$ V to 2.7 V	-	-	0.7	V
		$V_{CC} = 2.7$ V to 3.6 V	-	-	0.8	V
		$V_{CC} = 4.5$ V to 5.5 V	-	-	$0.3 \times V_{CC}$	V
V_{OH}	HIGH-state output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -100$ µA; $V_{CC} = 1.65$ V to 5.5 V	$V_{CC} - 0.1$	-	-	V
		$I_O = -4$ mA; $V_{CC} = 1.65$ V	0.95	-	-	V
		$I_O = -8$ mA; $V_{CC} = 2.3$ V	1.7	-	-	V
		$I_O = -12$ mA; $V_{CC} = 2.7$ V	1.9	-	-	V
		$I_O = -24$ mA; $V_{CC} = 3.0$ V	2.0	-	-	V
		$I_O = -32$ mA; $V_{CC} = 4.5$ V	3.4	-	-	V
V_{OL}	LOW-state output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 100$ µA; $V_{CC} = 1.65$ V to 5.5 V	-	-	0.1	V
		$I_O = 4$ mA; $V_{CC} = 1.65$ V	-	-	0.70	V
		$I_O = 8$ mA; $V_{CC} = 2.3$ V	-	-	0.45	V
		$I_O = 12$ mA; $V_{CC} = 2.7$ V	-	-	0.60	V
		$I_O = 24$ mA; $V_{CC} = 3.0$ V	-	-	0.80	V
		$I_O = 32$ mA; $V_{CC} = 4.5$ V	-	-	0.80	V
I_{LI}	input leakage current	$V_I = 5.5$ V or GND; $V_{CC} = 5.5$ V	-	-	±20	µA
I_{OFF}	power-off leakage current	V_I or $V_O = 5.5$ V; $V_{CC} = 0$ V	-	-	±20	µA
I_{CC}	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 5.5$ V	-	-	40	µA
ΔI_{CC}	additional quiescent supply current	per pin; $V_I = V_{CC} - 0.6$ V; $I_O = 0$ A; $V_{CC} = 2.3$ V to 5.5 V	-	-	5000	µA

[1] All typical values are measured at $T_{amb} = 25$ °C.

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11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8.

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
T_{amb} = −40 °C to +85 °C[1]							
t_{PHL}, t_{PLH}	propagation delay input nA, nB to output nY	see Figure 7					
		V_{CC} = 1.65 V to 1.95 V		1.0	3.2	9.0	ns
		V_{CC} = 2.3 V to 2.7 V		0.5	2.2	5.1	ns
		V_{CC} = 2.7 V		1.0	2.5	5.3	ns
		V_{CC} = 3.0 V to 3.6 V		0.5	2.1	4.7	ns
		V_{CC} = 4.5 V to 5.5 V		0.5	1.7	3.8	ns
C_{PD}	power dissipation capacitance	per gate; V_I = GND to V_{CC}	[2]	-	14.4	-	pF
T_{amb} = −40 °C to +125 °C							
t_{PHL}, t_{PLH}	propagation delay input nA, nB to output nY	see Figure 7					
		V_{CC} = 1.65 V to 1.95 V		1.0	-	11.3	ns
		V_{CC} = 2.3 V to 2.7 V		0.5	-	6.4	ns
		V_{CC} = 2.7 V		1.0	-	6.7	ns
		V_{CC} = 3.0 V to 3.6 V		0.5	-	5.9	ns
		V_{CC} = 4.5 V to 5.5 V		0.5	-	4.8	ns

[1] All typical values are measured at nominal V_{CC} and T_{amb} = 25 °C.

[2] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

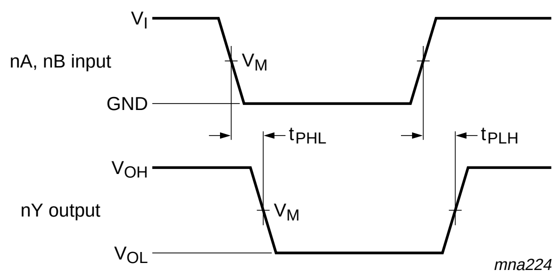
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms



Measurement points are given in Table 9.

V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig 7. Input (nA, nB) to output (nY) propagation delays

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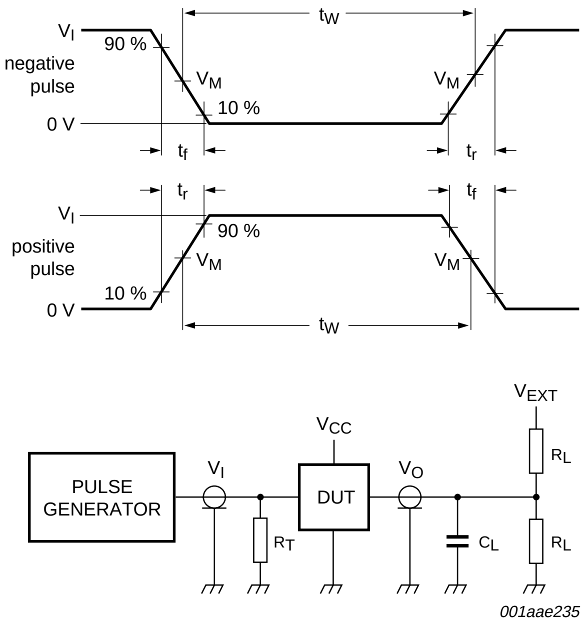
Table 9. Measurement points

Supply voltage	Input	Output
V_{CC}	V_M	V_M
1.65 V to 1.95 V	$0.5V_{CC}$	$0.5V_{CC}$
2.3 V to 2.7 V	$0.5V_{CC}$	$0.5V_{CC}$
2.7 V	1.5 V	1.5 V
3.0 V to 3.6 V	1.5 V	1.5 V
4.5 V to 5.5 V	$0.5V_{CC}$	$0.5V_{CC}$



Test data is given in Table 10.

Definitions for test circuit:

R_L = Load resistor

C_L = Load capacitance including jig and probe capacitance

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator

V_{EXT} = Test voltage for switching times

Fig 8. Load circuitry for switching times

Table 10. Test data

Supply voltage	Input		Load		V_{EXT}
V_{CC}	V_I	t_r, t_f	C_L	R_L	t_{PLH}, t_{PHL}
1.65 V to 1.95 V	V_{CC}	≤ 2.0 ns	30 pF	1 kΩ	open
2.3 V to 2.7 V	V_{CC}	≤ 2.0 ns	30 pF	500 Ω	open
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open
4.5 V to 5.5 V	V_{CC}	≤ 2.5 ns	50 pF	500 Ω	open

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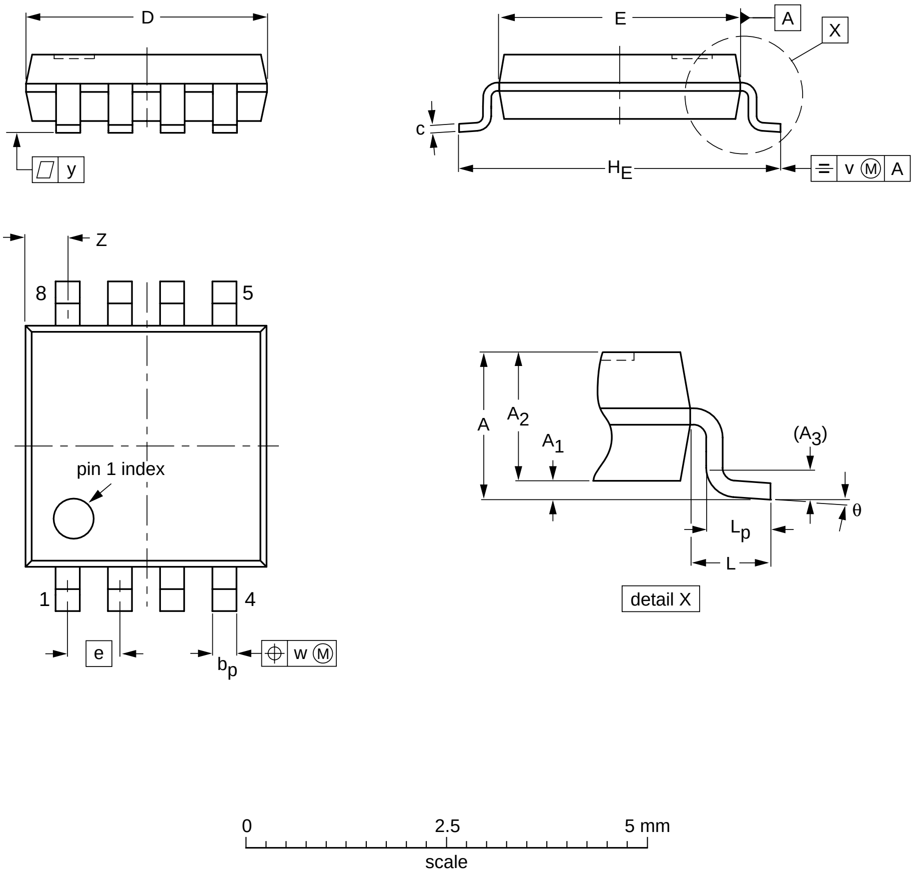
13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm **SOT505-2**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D(1)	E(1)	e	H_E	L	L_p	v	w	y	Z(1)	θ
mm	1.1	0.15 0.00	0.95 0.75	0.25	0.38 0.22	0.18 0.08	3.1 2.9	3.1 2.9	0.65	4.1 3.9	0.5	0.47 0.33	0.2	0.13	0.1	0.70 0.35	8° 0°

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT505-2		- - -				02-01-16

Fig 9. Package outline SOT505-2 (TSSOP8)

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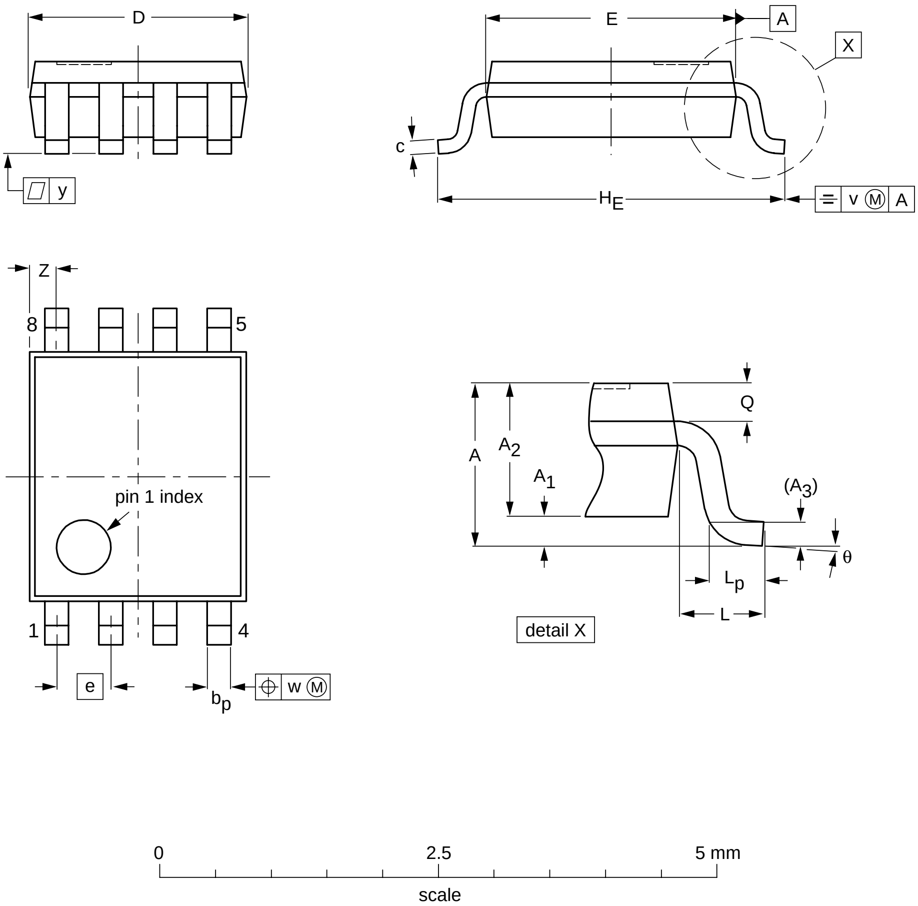
VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm **SOT765-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D(1)	E(2)	e	H_E	L	L_p	Q	v	w	y	Z(1)	θ
mm	1	0.15 0.00	0.85 0.60	0.12	0.27 0.17	0.23 0.08	2.1 1.9	2.4 2.2	0.5	3.2 3.0	0.4	0.40 0.15	0.21 0.19	0.2	0.13	0.1	0.4 0.1	8° 0°

Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT765-1		MO-187				02-06-07

Fig 10. Package outline SOT765-1 (VSSOP8)

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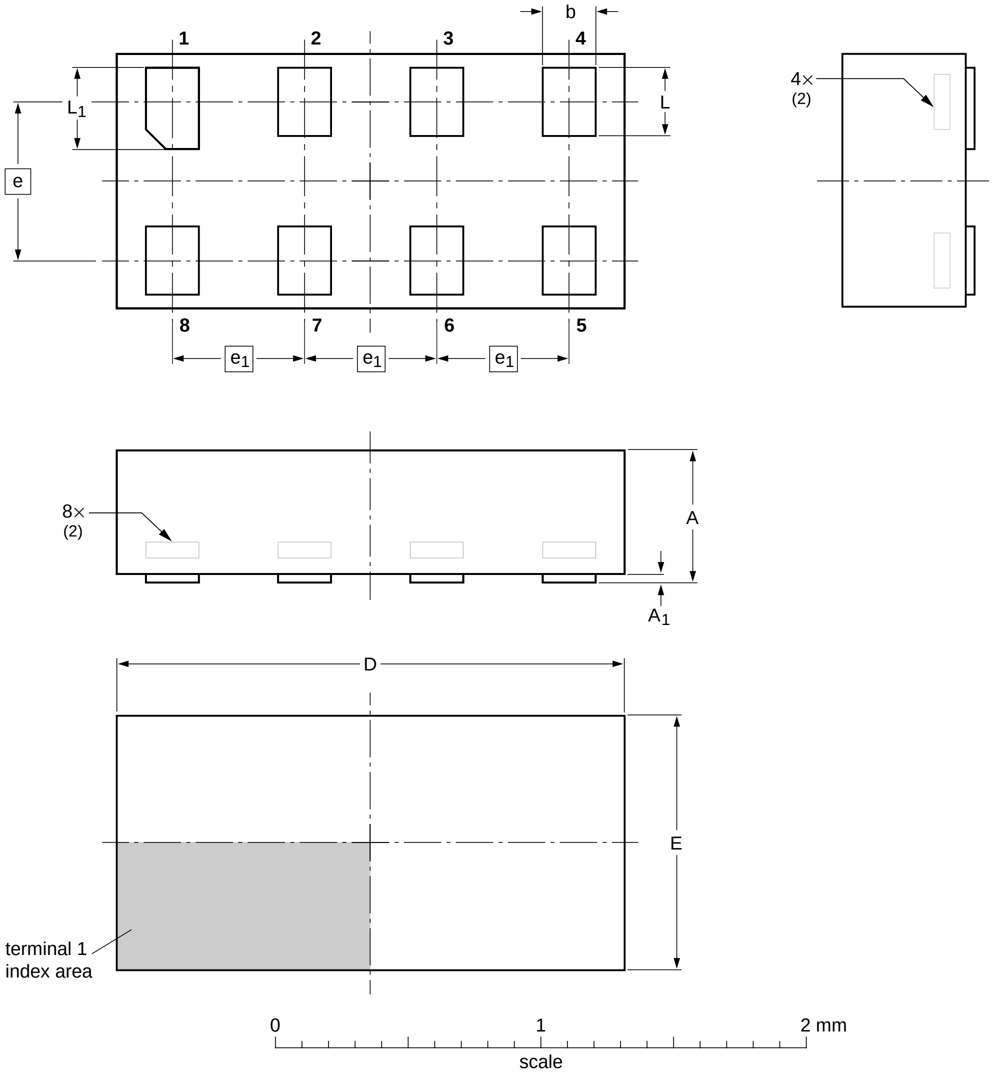
XSON8: plastic extremely thin small outline package; no leads; 8 terminals; body 1 x 1.95 x 0.5 mm **SOT833-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A (1) max	A_1 max	b	D	E	e	e_1	L	L_1
mm	0.5	0.04	0.25 0.17	2.0 1.9	1.05 0.95	0.6	0.5	0.35 0.27	0.40 0.32

Notes

1. Including plating thickness.
2. Can be visible in some manufacturing processes.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT833-1	- - -	MO-252	- - -			~~04-07-22~~ 04-11-09

Fig 11. Package outline SOT833-1 (XSON8)

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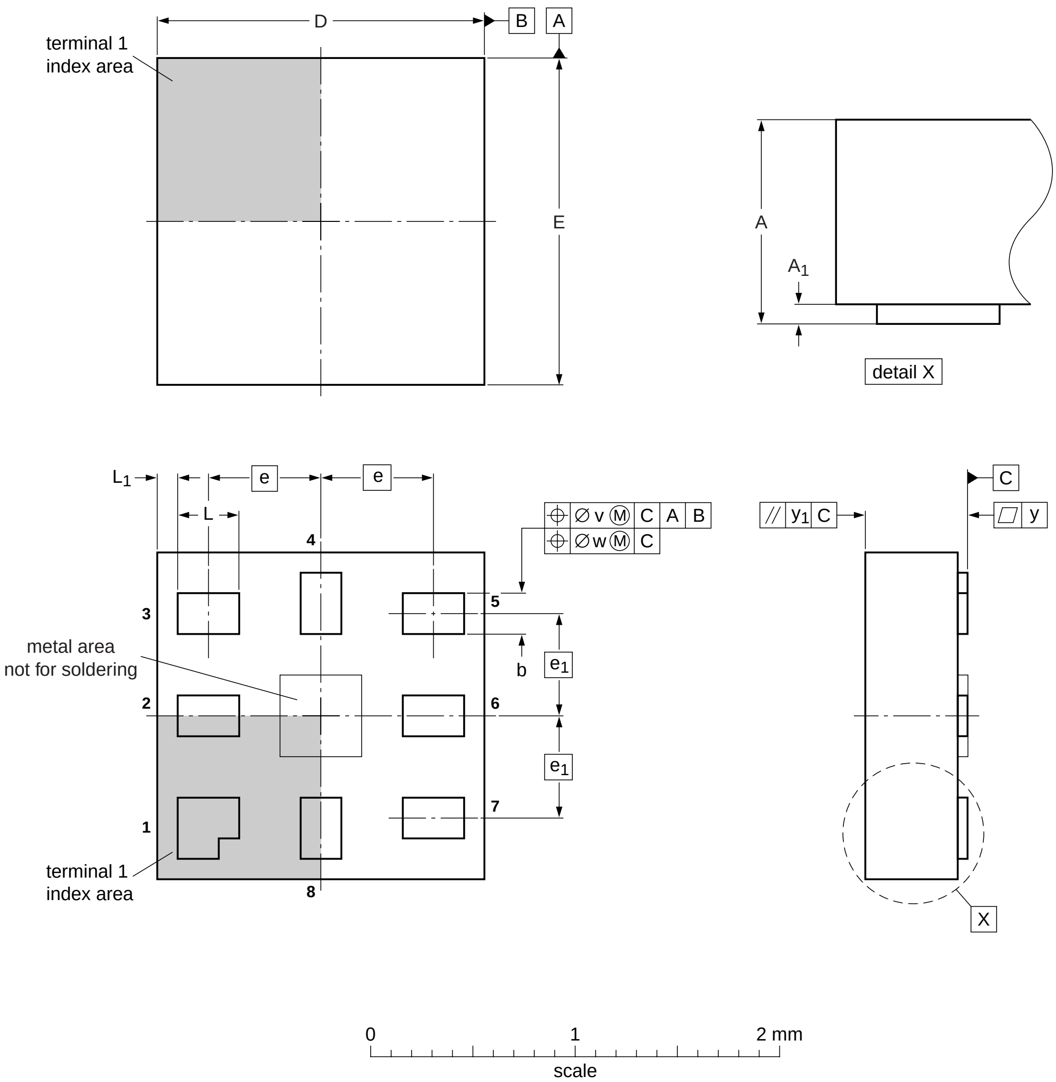
XQFN8: plastic extremely thin quad flat package; no leads; 8 terminals; body 1.6 x 1.6 x 0.5 mm **SOT902-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max	A_1	b	D	E	e	e_1	L	L_1	v	w	y	y_1
mm	0.5	0.05 0.00	0.25 0.15	1.65 1.55	1.65 1.55	0.55	0.5	0.35 0.25	0.15 0.05	0.1	0.05	0.05	0.05

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT902-1	- - -	MO-255	- - -			~~05-11-16~~ 05-11-25

Fig 12. Package outline SOT902-1 (XQFN8)

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14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC2G08_5	20060515	Product data sheet	-	74LVC2G08_4
Modifications:	• The format of this data sheet has been redesigned to comply with the new presentation and information standard of Philips Semiconductors. • Added: type number 74LVC2G08GM (XQFN8 package)			
74LVC2G08_4 (9397 750 14533)	20050201	Product specification	-	74LVC2G08_3
74LVC2G08_3 (9397 750 13776)	20040915	Product specification	-	74LVC2G08_2
74LVC2G08_2 (9397 750 12175)	20031020	Product specification	-	74LVC2G08_1
74LVC2G08_1 (9397 750 11849)	20030825	Product specification	-	-

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16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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